

# MC74VHC139



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## Dual 2-to-4 Decoder/ Demultiplexer

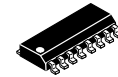
The MC74VHC139 is an advanced high speed CMOS 2-to-4 decoder/ demultiplexer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

When the device is enabled ( $\bar{E} = \text{low}$ ), it can be used for gating or as a data input for demultiplexing operations. When the enable input is held high, all four outputs are fixed high, independent of other inputs.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7V, allowing the interface of 5V systems to 3V systems.

- High Speed:  $t_{PD} = 5.0\text{ns}$  (Typ) at  $V_{CC} = 5\text{V}$
- Low Power Dissipation:  $I_{CC} = 4\mu\text{A}$  (Max) at  $T_A = 25^\circ\text{C}$
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2V to 5.5V Operating Range
- Low Noise:  $V_{OLP} = 0.8\text{V}$  (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V; Machine Model > 200V
- Chip Complexity: 100 FETs or 25 Equivalent Gates

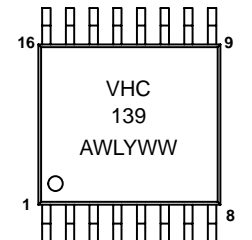
### MARKING DIAGRAMS



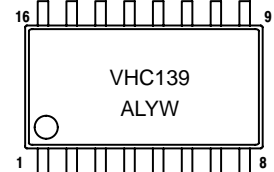
SOIC-16  
D SUFFIX  
CASE 751B



TSSOP-16  
DT SUFFIX  
CASE 948F



SOIC EIAJ-16  
M SUFFIX  
CASE 966



A = Assembly Location  
WL = Wafer Lot  
YY = Year  
WW = Work Week

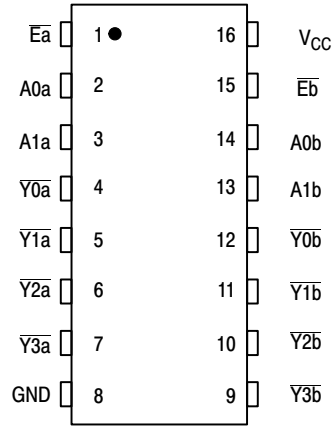
A = Assembly Location A = Assembly Location  
WL = Wafer Lot L = Wafer Lot  
Y = Year Y = Year  
WW = Work Week W = Work Week

### ORDERING INFORMATION

Device	Package	Shipping
MC74VHC139D	SOIC-16	48 Units/Rail
MC74VHC139DR2	SOIC-16	2500 Units/Reel
MC74VHC139DT	TSSOP-16	96 Units/Rail
MC74VHC139DTEL	TSSOP-16	2000 Units/Reel
MC74VHC139DTR2	TSSOP-16	2000 Units/Reel
MC74VHC139M	SOIC EIAJ-16	48 Units/Rail
MC74VHC139MEL	SOIC EIAJ-16	2000 Units/Reel

# MC74VHC139

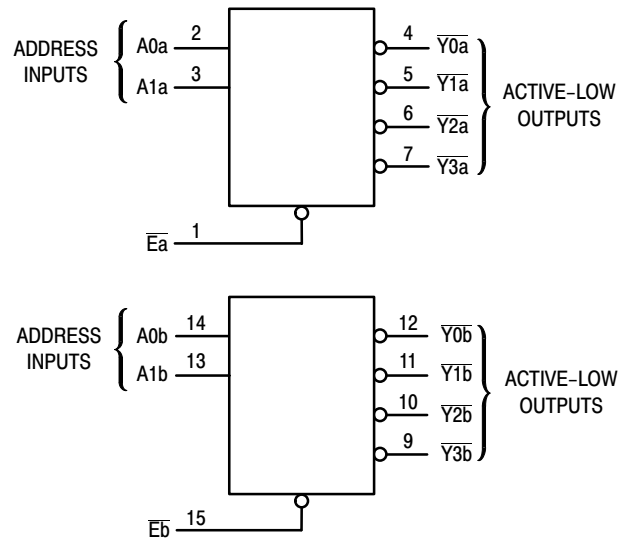
## PIN ASSIGNMENT



## FUNCTION TABLE

Inputs			Outputs			
$\bar{E}$	A1	A0	$\bar{Y0}$	$\bar{Y1}$	$\bar{Y2}$	$\bar{Y3}$
H	X	X	H	H	H	H
L	L	L	L	H	H	H
L	L	H	H	L	H	H
L	H	L	H	H	L	H
L	H	H	H	H	H	L

## LOGIC DIAGRAM



# MC74VHC139

## EXPANDED LOGIC DIAGRAM (1/2 OF DEVICE)

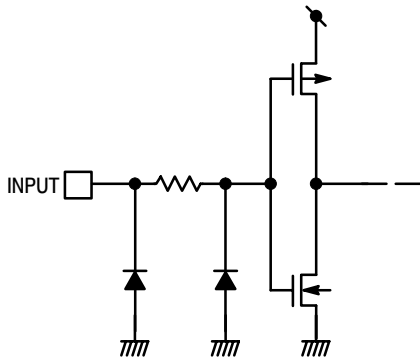
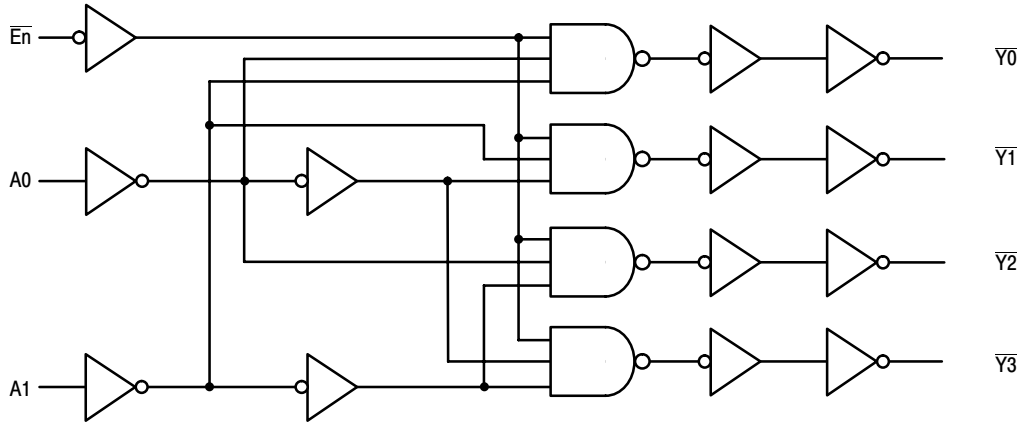
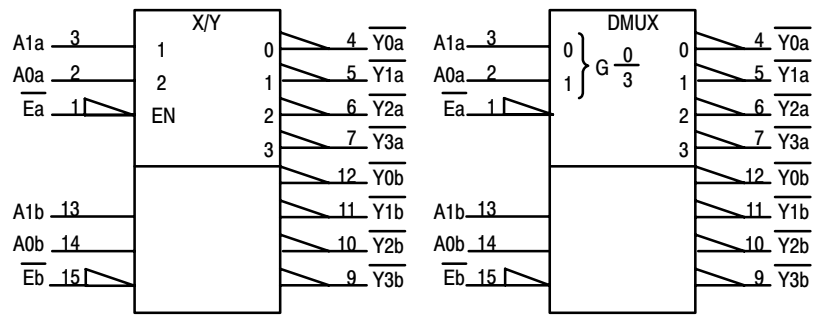


Figure 1. Input Equivalent Circuit

## IEC LOGIC DIAGRAM





# MC74VHC139

## DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V <sub>CC</sub> (V)	T <sub>A</sub> = 25°C			T <sub>A</sub> = ≤ 85°C		T <sub>A</sub> = ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0	1.5			1.5		1.5		V
			3.0	2.1			2.1		2.1		
			4.5	3.15			3.15		3.15		
			5.5	3.85			3.85		3.85		
V <sub>IL</sub>	Maximum Low-Level Input Voltage		2.0			0.5		0.5		0.5	V
			3.0			0.9		0.9		0.9	
			4.5			1.35		1.35		1.35	
			5.5			1.65		1.65		1.65	
V <sub>OH</sub>	Minimum High-Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OH</sub> = -50 μA	2.0	1.9	2.0		1.9		1.9		V
			3.0	2.9	3.0		2.9		2.9		
			4.5	4.4	4.5		4.4		4.4		
		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OH</sub> = -4 mA I <sub>OH</sub> = -8 mA	3.0	2.58			2.48		2.34		
			4.5	3.94			3.80		3.66		
V <sub>OL</sub>	Maximum Low-Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OL</sub> = 50 μA	2.0		0.0	0.1		0.1		0.1	V
			3.0		0.0	0.1		0.1		0.1	
			4.5		0.0	0.1		0.1		0.1	
		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OL</sub> = 4 mA I <sub>OL</sub> = 8 mA	3.0			0.36		0.44		0.52	
			4.5			0.36		0.44		0.52	
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0		μA	
I <sub>CC</sub>	Maximum Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5		4.0		40.0		40.0	μA	

## AC ELECTRICAL CHARACTERISTICS (Input t<sub>r</sub> = t<sub>f</sub> = 3.0ns)

Symbol	Parameter	Test Conditions	T <sub>A</sub> = 25°C			T <sub>A</sub> = -40 to 85°C		T <sub>A</sub> = -55 to 125°C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, A to Y	V <sub>CC</sub> = 3.3 ± 0.3 V C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		7.2	11.0	1.0	13.0	1.0	13.0	ns
				9.7	14.5	1.0	16.5	1.0	16.5	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, A to Y	V <sub>CC</sub> = 5.0 ± 0.5 V C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		5.0	7.2	1.0	8.5	1.0	8.5	ns
				6.5	9.2	1.0	10.5	1.0	10.5	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, E to Y	V <sub>CC</sub> = 3.3 ± 0.3 V C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		6.4	9.2	1.0	11.0	1.0	11.0	ns
				8.9	12.7	1.0	14.5	1.0	14.5	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, E to Y	V <sub>CC</sub> = 5.0 ± 0.5 V C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		4.4	6.3	1.0	7.5	1.0	7.5	ns
				5.9	8.3	1.0	9.5	1.0	9.5	
C <sub>IN</sub>	Maximum Input Capacitance			4	10		10		10	pF

C <sub>PD</sub>	Power Dissipation Capacitance (1.)	Typical @ 25°C, V <sub>CC</sub> = 5.0V		pF
		26		

1. C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>/2 (per decoder). C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

# MC74VHC139

## SWITCHING WAVEFORMS

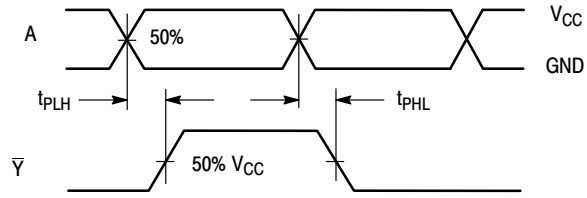


Figure 3.

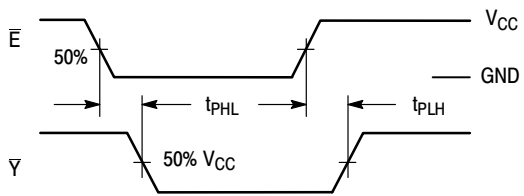
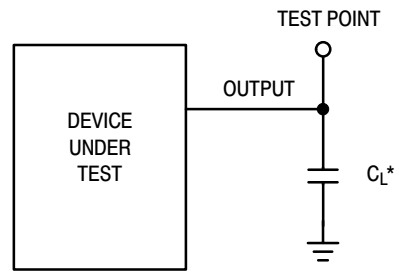


Figure 4.



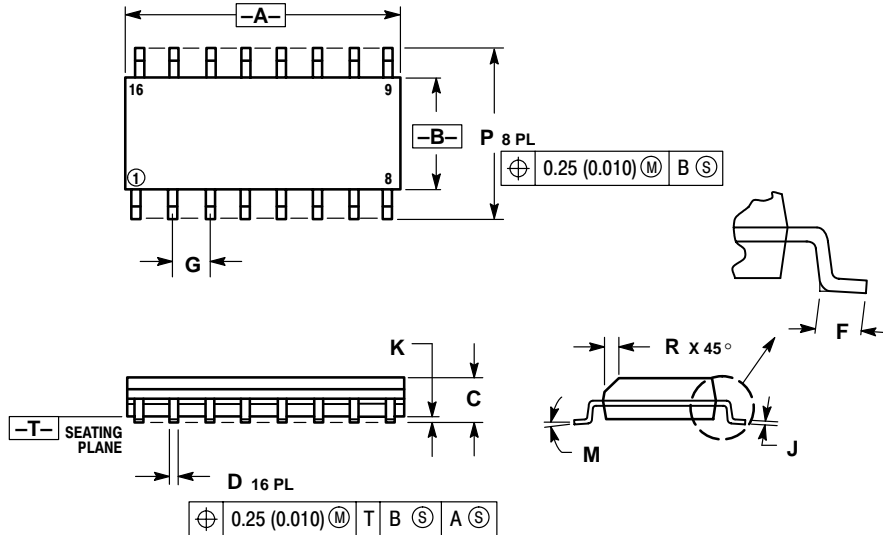
\*Includes all probe and jig capacitance

Figure 5. Test Circuit

# MC74VHC139

## PACKAGE DIMENSIONS

### D SUFFIX SOIC CASE 751B-05 ISSUE J

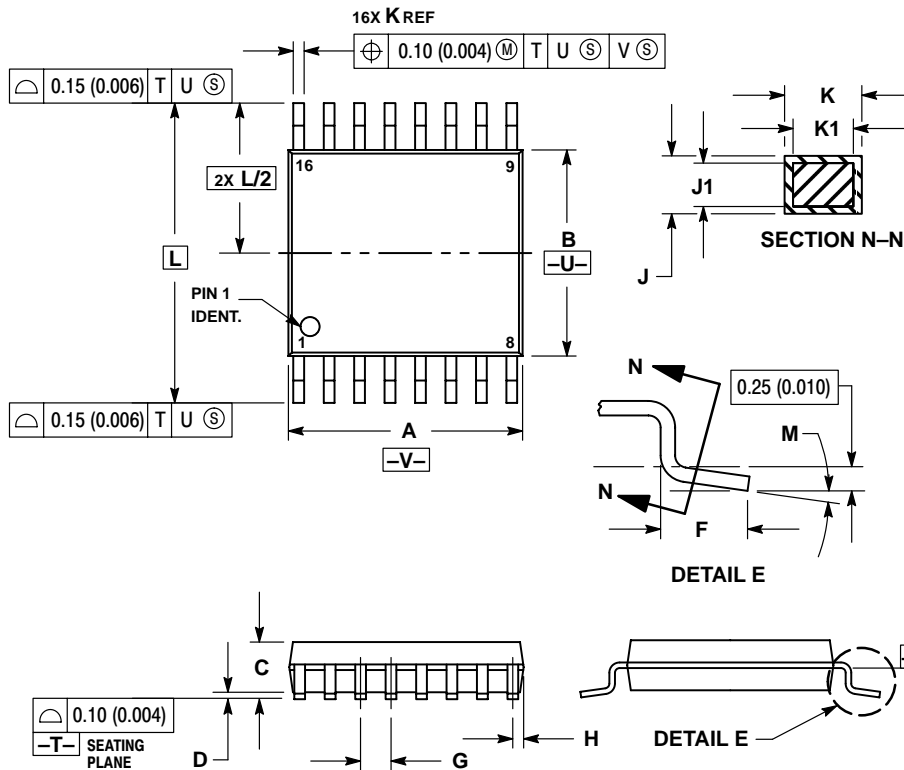


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

### DT SUFFIX TSSOP CASE 948F-01 ISSUE O



NOTES:

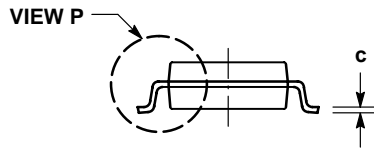
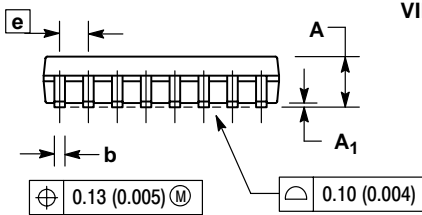
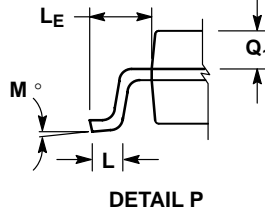
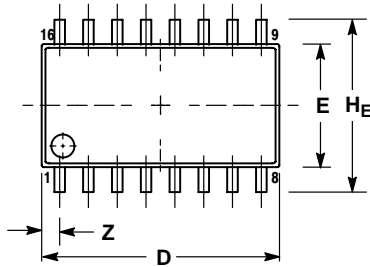
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

# MC74VHC139

## PACKAGE DIMENSIONS


### M SUFFIX SOIC EIAJ-16 CASE 966-01 ISSUE O



#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0°	10°	0°	10°
Q <sub>1</sub>	0.70	0.90	0.028	0.035
Z	---	0.78	---	0.031

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